



PRODUCT BULLETIN # 20251

Generic Copy

Issue Date: 08-Oct-2013

TITLE: Datasheet change for NE5532-D

PROPOSED FIRST SHIP DATE: 08-Oct-2013

AFFECTED CHANGE CATEGORY(S): Datasheet revision

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor sales office or <Juraj.Frohlich@onsemi.com>

NOTIFICATION TYPE:

ON Semiconductor considers this change approved unless specific conditions of acceptance are provided in writing. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

ON Semiconductor is notifying about a data sheet revision for the NE5532-D. As a result of additional device characterization, the input bias current (IB) parameter at room temperature is going to be corrected. Typical value of the IB parameter will be changed from current 200nA to 300nA for all device versions and there will be corrected also IB Max limit from 400nA to 500nA for the SE5532/A version.

| Characteristic | Symbol | Test Conditions | SE5532/A | | | NE5532/A, SA5532 | | | Unit |
|----------------|---------------------|-----------------|----------|--------------------|--------------------|------------------|--------------------|------|-------|
| | | | Min | Typ | Max | Min | Typ | Max | |
| Input Current | I _B | - | - | 200 300 | 400 500 | - | 200 300 | 800 | nA |
| | | Overtemperature | - | - | 700 | - | - | 1000 | nA |
| | ΔI _B /ΔT | - | - | 5.0 | - | - | 5.0 | - | nA/°C |

List of affected Parts:

SE5532AD8G
 SE5532AD8R2G
 SE5532NG